

Silicon PNP Power Transistors

2SA753

DESCRIPTION

- With TO-3 package
- Wide area of safe operation
- Complement to type 2SC1343

APPLICATIONS

- For 100W audio amplifier power output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

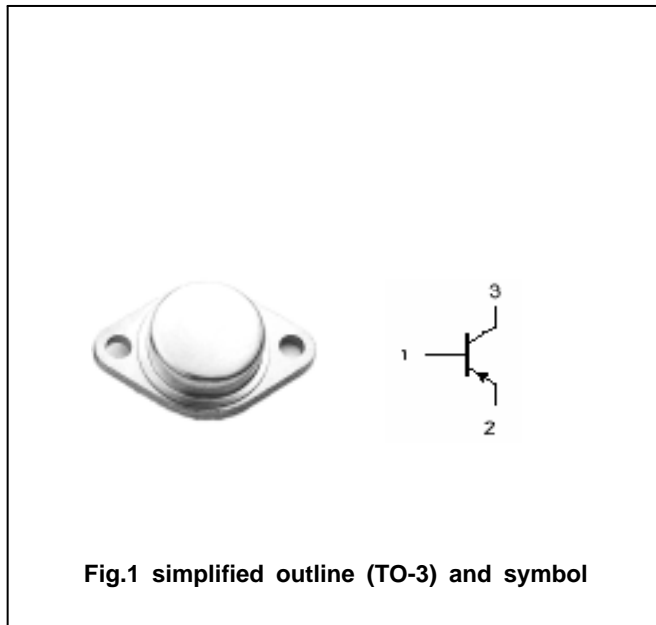


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-140	V
V_{CEO}	Collector-emitter voltage	Open base	-110	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-10	A
I_{CM}	Collector current-peak		-12	A
P_C	Collector power dissipation	$T_C=25$	100	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; R _{BE} =	-110			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA ; I _E =0	-140			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A ; I _B =-1A			-1.5	V
V _{BE}	Base-emitter on voltage	I _C =-1A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-30V ; I _E =0			-1	mA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-5V	30		200	
h _{FE-2}	DC current gain	I _C =-10A ; V _{CE} =-5V	15			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		20		MHz

◆ h_{FE-1} Classifications

A	B	C
30-60	50-120	100-200

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)